## **Electronic Supplementary Information (ESI) for**

## Preparation of Sn-doped CuAlS2 films with an intermediate band

## and wide-spectrum solar response

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Figure S1. (a) Sn-doped  $CuAlS_2$  films with different EPD time; (b) The influence of EPD time on the film thickness



**Figure S2.** (a) Top view SEM image of CuAlS<sub>2</sub> film; (b) Side view SEM image of CuAlS<sub>2</sub> film; (c) Top view SEM image of CuAl<sub>0.98</sub>Sn<sub>0.02</sub>S<sub>2</sub> film; (d) Side view SEM image of CuAl<sub>0.98</sub>Sn<sub>0.02</sub>S<sub>2</sub> film; (e) Top view SEM image of CuAl<sub>0.96</sub>Sn<sub>0.04</sub>S<sub>2</sub> film; (f) Side view SEM image of CuAl<sub>0.96</sub>Sn<sub>0.04</sub>S<sub>2</sub> film.



Figure S3. EDS spectrum and element analysis result of CuAl<sub>0.96</sub>Sn<sub>0.04</sub>S<sub>2</sub> films.